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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

Cautions

Keep safety first in your circuit designs!

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2SJ160, 2SJ161, 2SJ162

Silicon P-Channel MOS FET



ADE-208-1182 (Z)
1st. Edition
Mar. 2001

Application

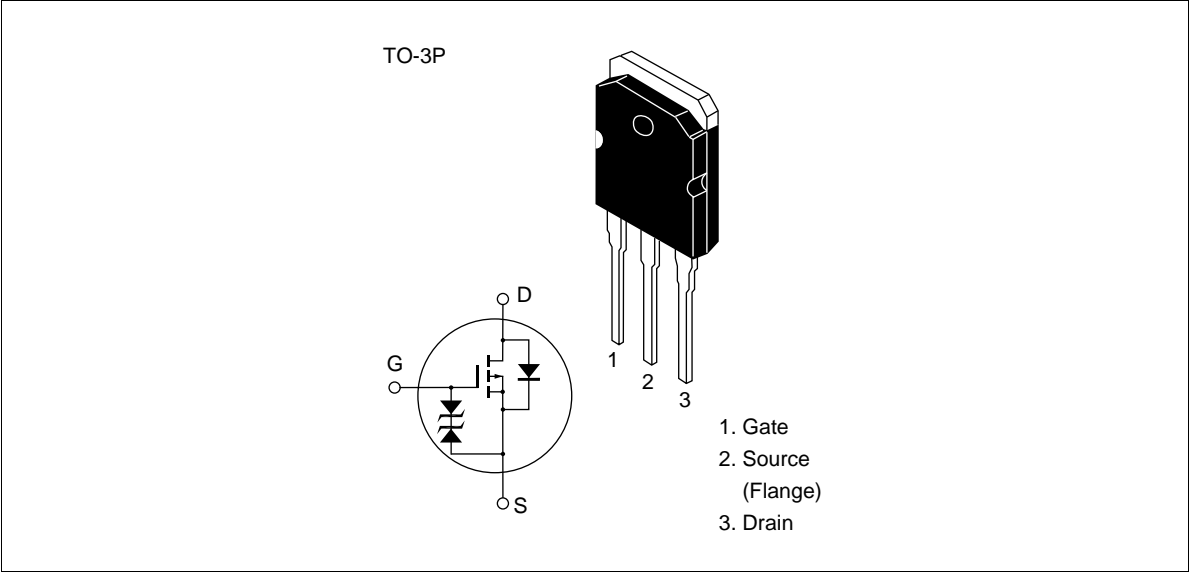
Low frequency power amplifier

Complementary pair with 2SK1056, 2SK1057 and 2SK1058

Features

- Good frequency characteristic
- High speed switching
- Wide area of safe operation
- Enhancement-mode
- Good complementary characteristics
- Equipped with gate protection diodes
- Suitable for audio power amplifier

Outline



Absolute Maximum Ratings (Ta = 25°C)

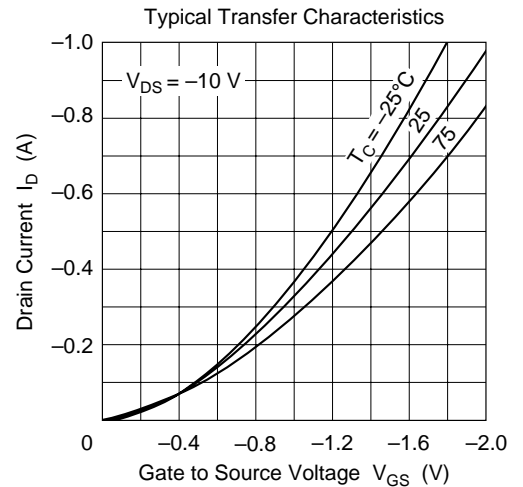
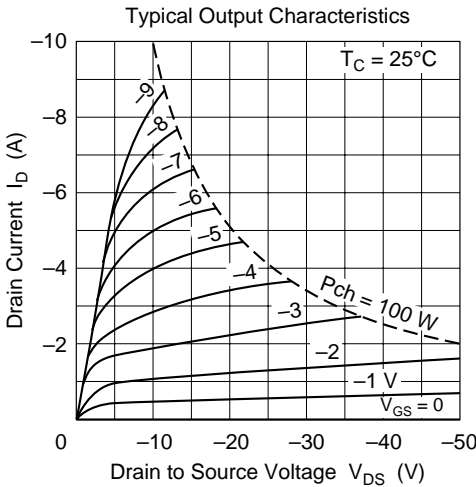
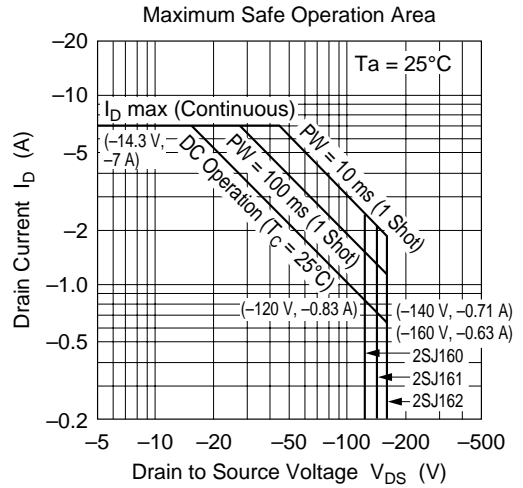
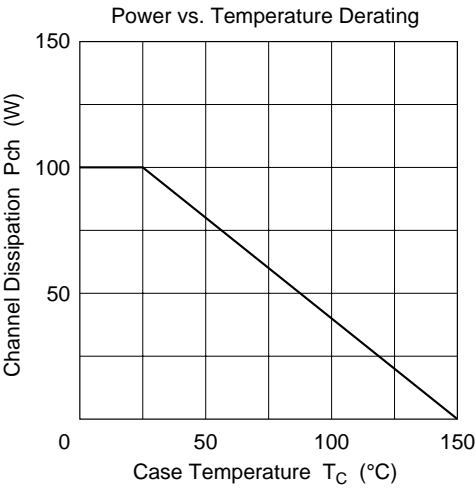
Item		Symbol	Ratings	Unit
Drain to source voltage	2SJ160	V_{DSX}	-120	V
	2SJ161		-140	
	2SJ162		-160	
Gate to source voltage		V_{GSS}	±15	V
Drain current		I_D	-7	A
Body to drain diode reverse drain current		I_{DR}	-7	A
Channel dissipation		P_{ch}^{*1}	100	W
Channel temperature		Tch	150	°C
Storage temperature		Tstg	-55 to +150	°C

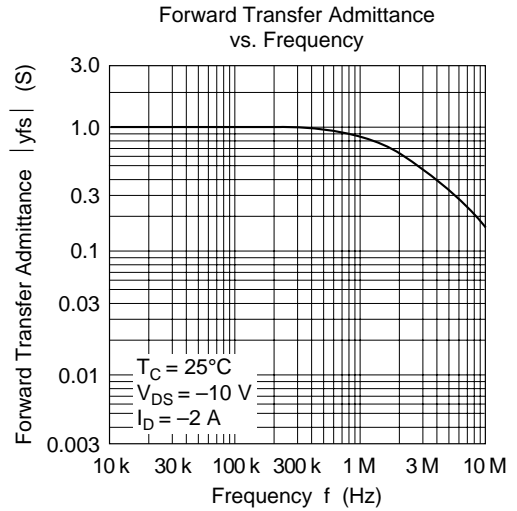
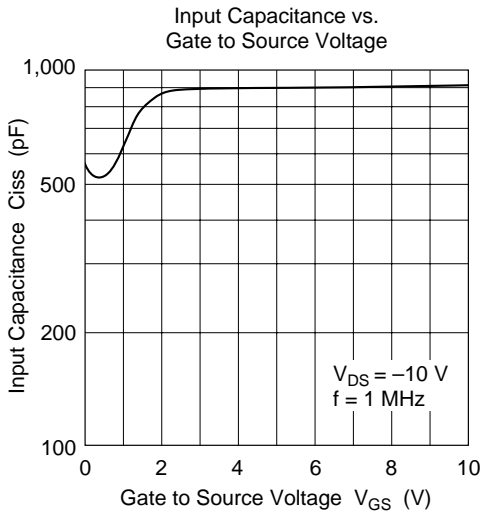
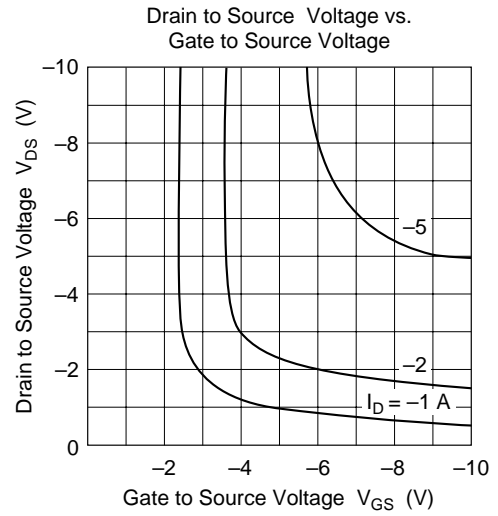
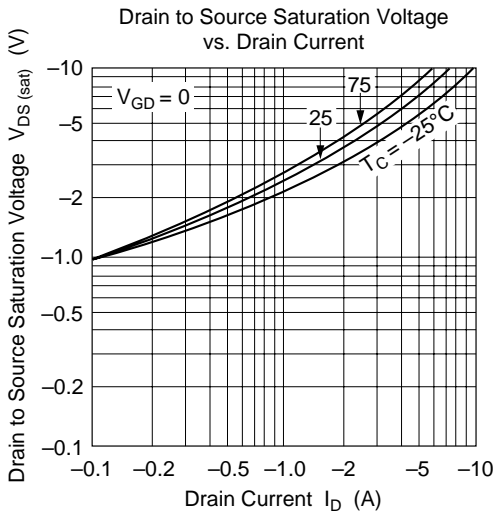
Note: 1. Value at T_c = 25°C

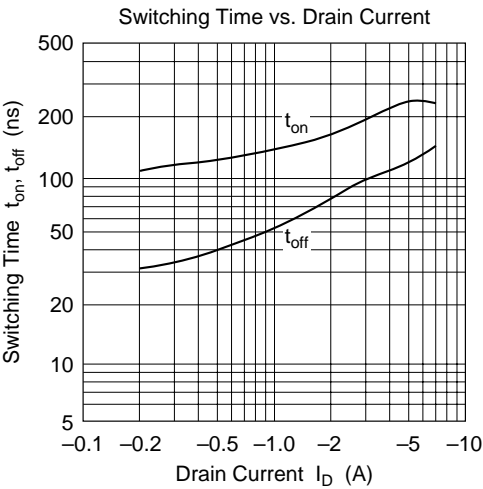
Electrical Characteristics (Ta = 25°C)

Item		Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	2SJ160	$V_{(BR)DSX}$	-120	—	—	V	$I_D = -10 \text{ mA}$, $V_{GS} = 10 \text{ V}$
	2SJ161		-140	—	—	V	
	2SJ162		-160	—	—	V	
Gate to source breakdown voltage		$V_{(BR)GSS}$	± 15	—	—	V	$I_G = \pm 100 \mu\text{A}$, $V_{DS} = 0$
Gate to source cutoff voltage		$V_{GS(off)}$	-0.15	—	-1.45	V	$I_D = -100 \text{ mA}$, $V_{DS} = -10 \text{ V}$
Drain to source saturation voltage		$V_{DS(sat)}$	—	—	-12	V	$I_D = -7 \text{ A}$, $V_{GD} = 0^{*1}$
Forward transfer admittance		$ y_{fs} $	0.7	1.0	1.4	S	$I_D = -3 \text{ A}$, $V_{DS} = -10 \text{ V}^{*1}$
Input capacitance		C_{iss}	—	900	—	pF	$V_{GS} = 5 \text{ V}$, $V_{DS} = -10 \text{ V}$, $f = 1 \text{ MHz}$
Output capacitance		C_{oss}	—	400	—	pF	
Reverse transfer capacitance		C_{rss}	—	40	—	pF	
Turn-on time		t_{on}	—	230	—	ns	$V_{DD} = -20 \text{ V}$, $I_D = -4 \text{ A}$
Turn-off time		t_{off}	—	110	—	ns	

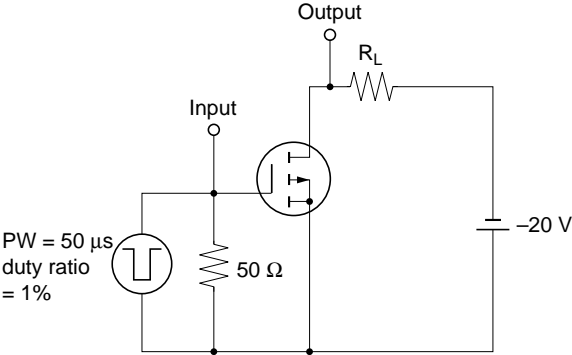
Note: 1. Pulse test



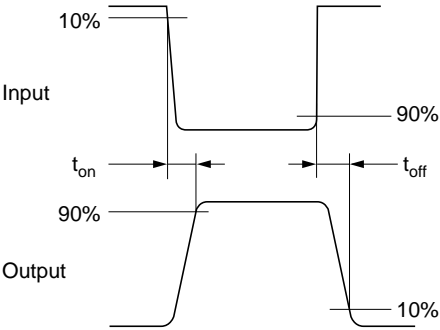




Switching Time Test Circuit

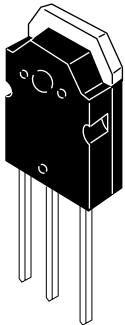
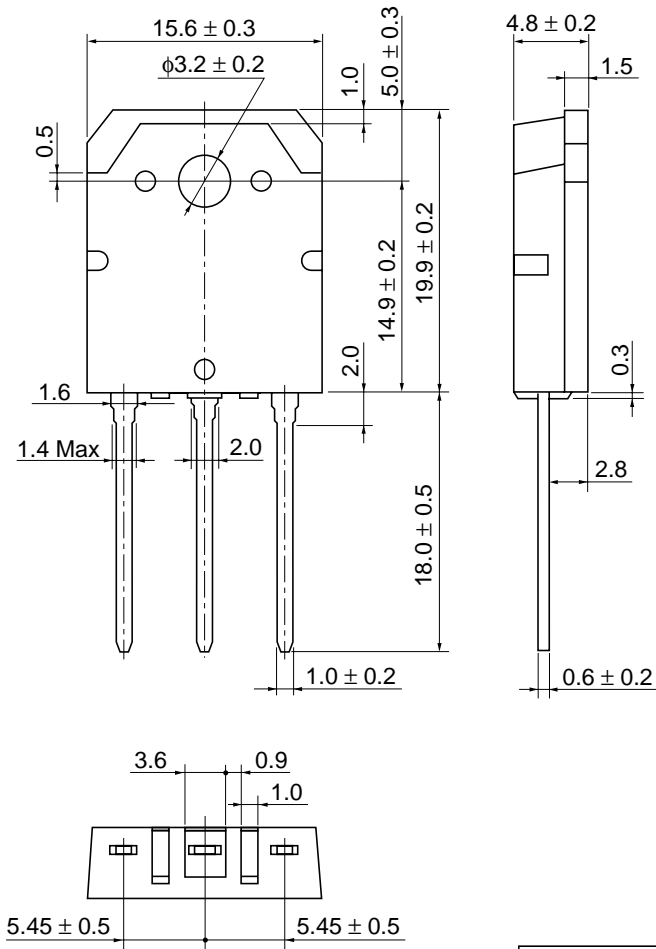


Waveforms



Package Dimensions

As of January, 2001
Unit: mm



Hitachi Code	TO-3P
JEDEC	—
EIAJ	Conforms
Mass (reference value)	5.0 g

Cautions

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HITACHI

Hitachi, Ltd.

Semiconductor & Integrated Circuits.

Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL	NorthAmerica	: http://semiconductor.hitachi.com/
	Europe	: http://www.hitachi-eu.com/hel/ecg
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For further information write to:Hitachi Semiconductor
(America) Inc.179 East Tasman Drive,
San Jose, CA 95134

Tel: <1> (408) 433-1990

Fax: <1> (408) 433-0223

Hitachi Europe GmbH
Electronic Components GroupDornacher Straße 3
D-85622 Feldkirchen, Munich

Germany

Tel: <49> (89) 9 9180-0

Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.

Electronic Components Group.

Whitebrook Park

Lower Cookham Road

Maidenhead

Berkshire SL6 8YA, United Kingdom

Tel: <44> (1628) 585000

Fax: <44> (1628) 585160

Hitachi Asia Ltd.

Hitachi Tower

16 Collyer Quay #20-00,

Singapore 049318

Tel: <65>-538-6533/538-8577

Fax: <65>-538-6933/538-3877

URL: <http://www.hitachi.com.sg>

Hitachi Asia Ltd.

(Taipei Branch Office)

4/F, No. 167, Tun Hwa North Road,

Hung-Kuo Building,

Taipei (105), Taiwan

Tel: <886>-(2)-2718-3666

Fax: <886>-(2)-2718-8180

Telex: 23222 HAS-TP

URL: <http://www.hitachi.com.tw>

Hitachi Asia (Hong Kong) Ltd.

Group III (Electronic Components)

7/F., North Tower,

World Finance Centre,

Harbour City, Canton Road

Tsim Sha Tsui, Kowloon,

Hong Kong

Tel: <852>-(2)-735-9218

Fax: <852>-(2)-730-0281

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